

描述 / Descriptions

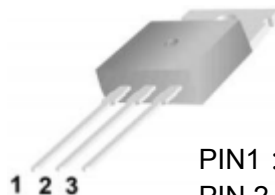
TO-220 塑封封装 双向可控硅。
 Triac in a TO-220 Plastic Package.

特征 / Features

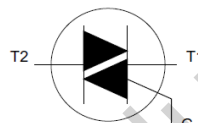
采用玻璃钝化技术，采用环氧塑脂塑料封装，四个信号区都可以满足高灵敏度需要。
 glass passivated, sensitive gate triacs in a plastic envelope, where high sensitivity is required in all four quadrants.

用途 / Applications

用于一般双向开关和相位控制。
 Use in general purpose bidirectional switching and phase control applications.



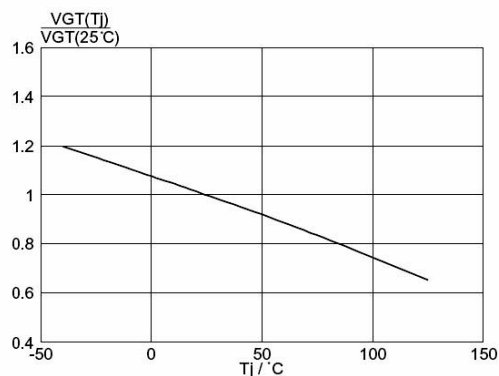
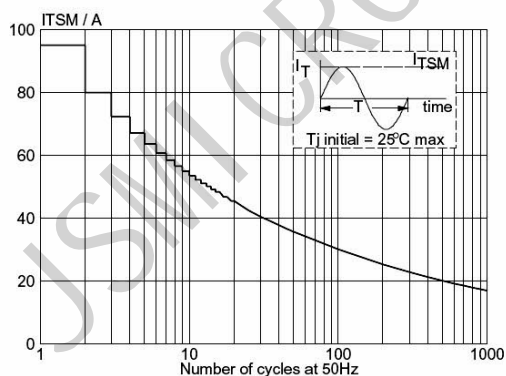
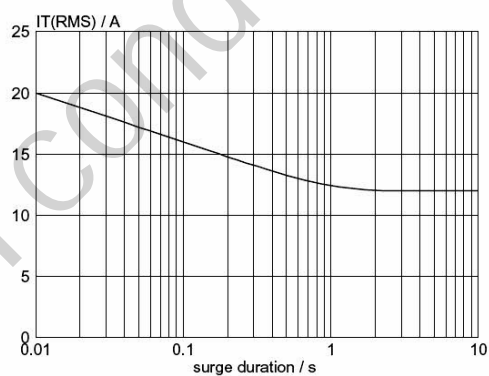
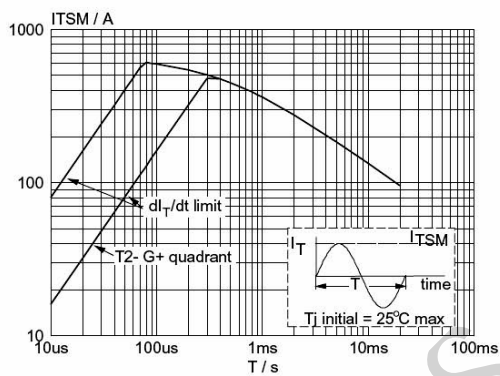
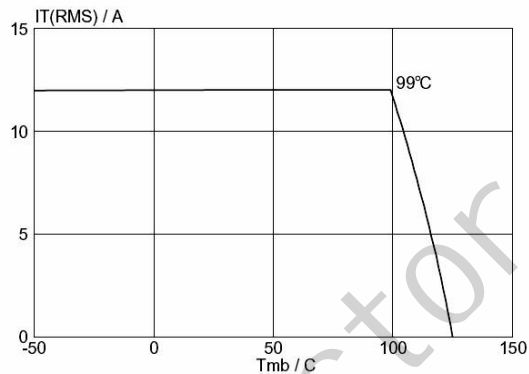
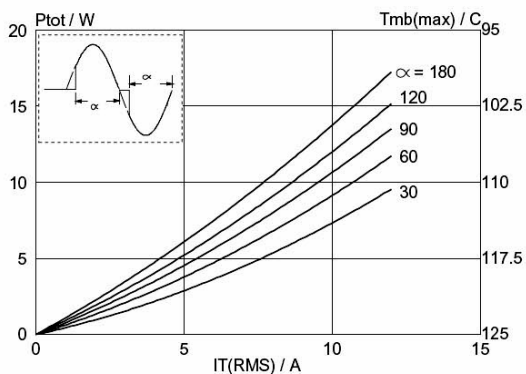
PIN1 : Main Terminal 1
 PIN 2 : Main Terminal 2
 PIN 3 : Gate


极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating		单位 Unit
		600	800	
Repetitive peak off-state voltages	V_{DRM} (T _J =25°C)	600	800	V
RMS on-state current	$I_{T(RMS)}$	12		A
Non-repetitive peak on-state current	$I_{TSM}(t=20ms)$	95		A
Non-repetitive peak on-state current	$I_{TSM}(t=16.7ms)$	105		A
I ² _t for fusing	$I^2t_{(t=10ms)}$	45		A ² S
Repetitive rate of rise of on-state current after triggering	$I_{TM}=12A$ $I_G=0.2A$ $dI_G/dt=0.2A/\mu s$	T2+G+	50	A/μS
		T2+G-	50	A/μS
		T2-G-	50	A/μS
		T2-G+	10	A/μS
Peak gate current	I_{GM}	2.0		A
Peak gate voltages	V_{GM}	5.0		V
Peak gate power	P_{GM}	5.0		W
Average gate power (Over any 20 ms period)	$P_{G(AV)}$	0.5		W
Junction Temperature	T_j	125		°C
Storage Temperature Range	T_{stg}	-40~150		°C
Thermal resistance junction to ambient	$R_{th(j-a)}$	60		K/W
Thermal resistance junction to mounting base	$R_{th(j-b)}$	1.5		K/W

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit	
Gate trigger current	I _{GT}	V _D =12V I _T =0.1A	T2+G+		2.5	10	mA
			T2+G-		4	10	
			T2-G-		5	10	
			T2-G+		11	25	
Latching current	I _L	V _D =12V I _G =0.1A	T2+G+			30	mA
			T2+G-			40	
			T2-G-			30	
			T2-G+			40	
Holding current	I _H	V _D =12V I _G =0.1A			30	mA	
On-state voltage	V _T	I _T =15A		1.4	1.65	V	
Gate trigger voltage	V _{GT}	V _D =12V I _T =0.1A		0.7	1.5	V	
		V _D =400V I _T =0.1A, T _J =125°C	0.25	0.4			
Off-state leakage current	I _D	V _D =V _{DRM(max)} T _J =125°C		0.1	0.5	mA	
Critical rate of rise of off-state current	t _{gt}	I _{TM} =16A V _D =V _{DRM(max)} I _G =0.1A dI _G /dt=5A/μs		2.0		μs	
Repetitive peak off-state current	dV _D /dt	V _{DM} =67% V _{DRM(MAX)} T _J =125°C		150		V/μs	

电参数曲线图 / Electrical Characteristic Curve


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